

VHF POWER MOSFET

Silicon N-Channel Enhancement Mode

DESCRIPTION:

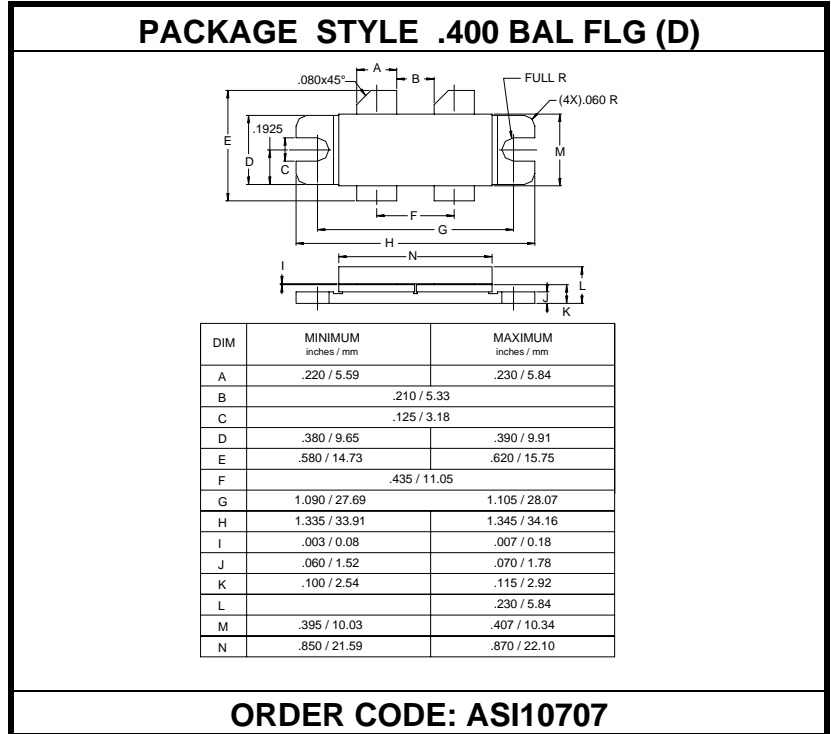
The **VFT300-28** is Designed for Wideband High Power VHF Amplifier Applications operating up to 250 MHz.

FEATURES:

- $P_G = 14$ dB Typical at 175 MHz
- $\eta_D = 55\%$ Typ. at $P_{OUT} = 300$ Watts
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_D	16 A
$V_{(BR)DSS}$	65 V
V_{DGR}	65 V
V_{GS}	± 40 V
P_{DISS}	500 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.35 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	$V_{GS} = 0$ V	$I_{DS} = 100$ mA		65			V
I_{DSS}	$V_{DS} = 28$ V	$V_{GS} = 0$ V				5.0	mA
I_{GSS}	$V_{DS} = 0$ V	$V_{GS} = 20$ V				1.0	μ A
V_{GS}	$V_{DS} = 10$ V	$I_D = 100$ mA		1.0		5.0	V
V_{DS}	$V_{GS} = 10$ V	$I_D = 10$ A				1.5	V
G_{FS}	$V_{DS} = 10$ V	$I_D = 5$ A		3500			mS
C_{iss} C_{oss} C_{rss}	$V_{GS} = 28$ V	$V_{DS} = 0$ V	$F = 1.0$ MHz		375 188 26		pF
G_{PS} η_D	$V_{DD} = 28$ V $f = 175$ MHz	$I_{DQ} = 2 \times 250$ mA	$P_{OUT} = 300$ W	12 50	14 55		dB %